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Abstract of the Disclosure

A semiconductor memory device includes a dielectric film, first and second wiring lines, a copper fuse section and an opening. The first and
5 second wiring lines are provided in the dielectric film. The copper fuse section is provided in the dielectric film, and is connected to the first and second wiring lines. The opening is formed to the copper fuse section through the dielectric film. A
10 laser beam is irradiated to the copper fuse section through the opening in an oxygen atmosphere.